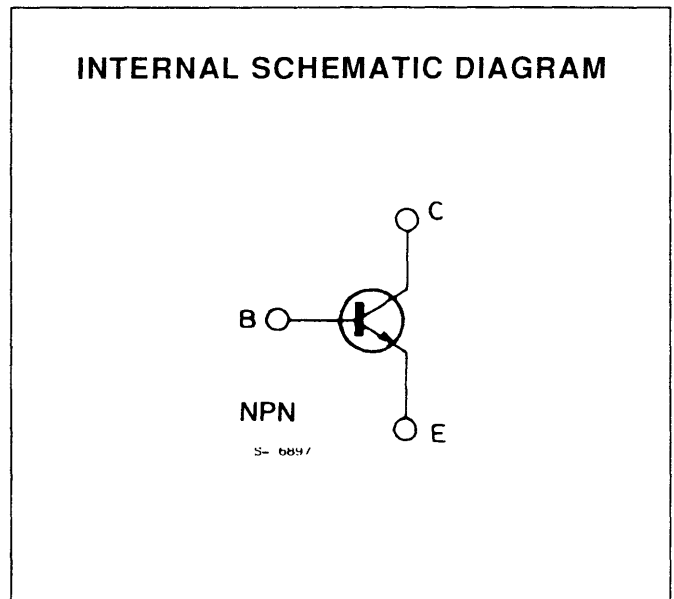
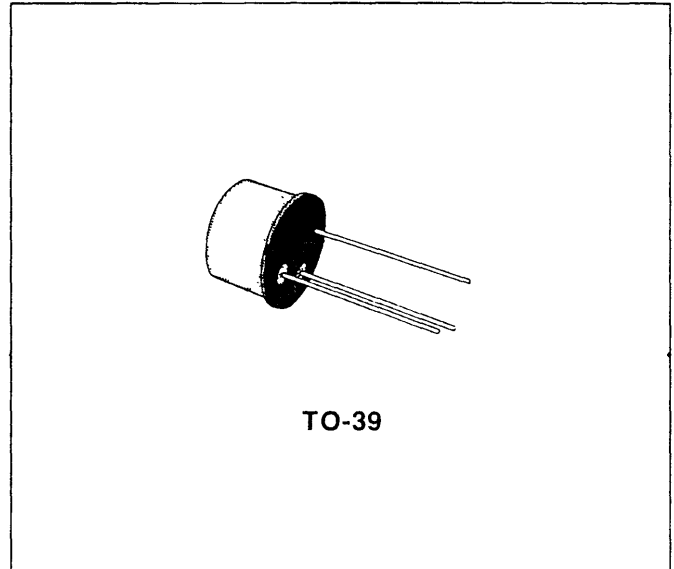


VHF OSCILLATOR POWER AMPLIFIER

DESCRIPTION

The 2N4427 and BFR98 are silicon planar epitaxial NPN transistor in Jedec TO-39 metal case. They are designed for VHF class A, B, or C amplifier and oscillator applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	40	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	20	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	3.5	V
I_C	Collector Current	0.5	A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25\text{ }^\circ\text{C}$	3.5	W
T_{stg}, T_J	Storage and Junction Temperature	- 65 to 200	$^\circ\text{C}$

THERMAL DATA

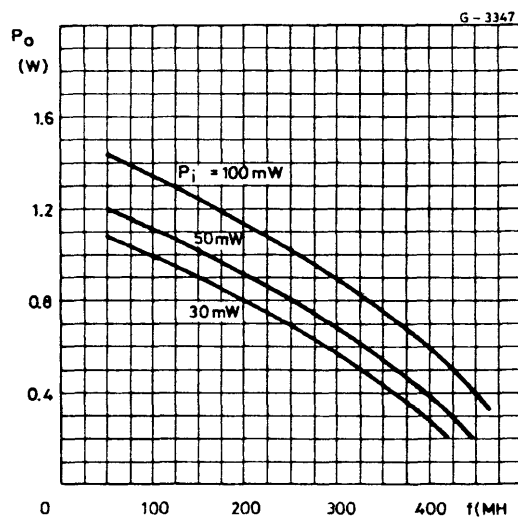
$R_{th J-case}$	Thermal Resistance Junction-case	Max	50	$^{\circ}C/W$
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ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

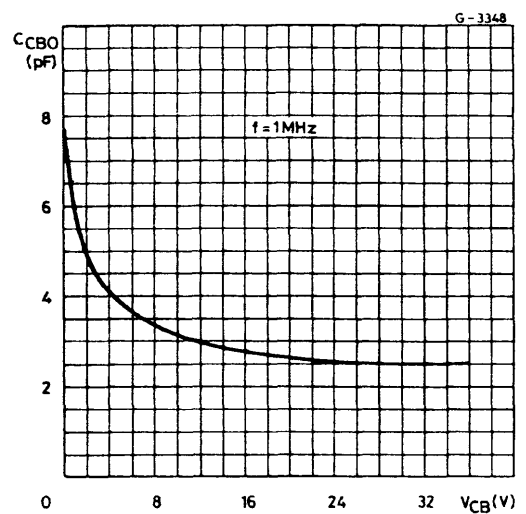
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	$V_{CE} = 12 V$			20	μA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100 \mu A$	40			V
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 5 mA$	20			V
$V_{CER(sus)}^*$	Collector-Emitter Sustaining Voltage ($R_{BE} = 10 \Omega$)	$I_C = 5 mA$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100 \mu A$	3.5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 100 mA$ $I_B = 20 mA$			0.5	V
h_{FE}^*	DC Current Gain	$I_C = 100 mA$ $V_{CE} = 5 V$ $I_C = 360 mA$ $V_{CE} = 5 V$	10 5		200	
f_T	Transition Frequency	$I_C = 50 mA$ $V_{CE} = 15 V$ $f = 200 MHz$	500			MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $V_{CB} = 12 V$ $f = 1 MHz$			4	pF
P_o^{**}	Output Power	$V_{CC} = 12 V$ $P_i = 100 mW$ $f = 175 MHz$	1			W
η^{**}	Collector Efficiency	$V_{CC} = 12 V$ $P_o = 1 W$ $f = 175 MHz$	50			%

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.
** See test circuit.

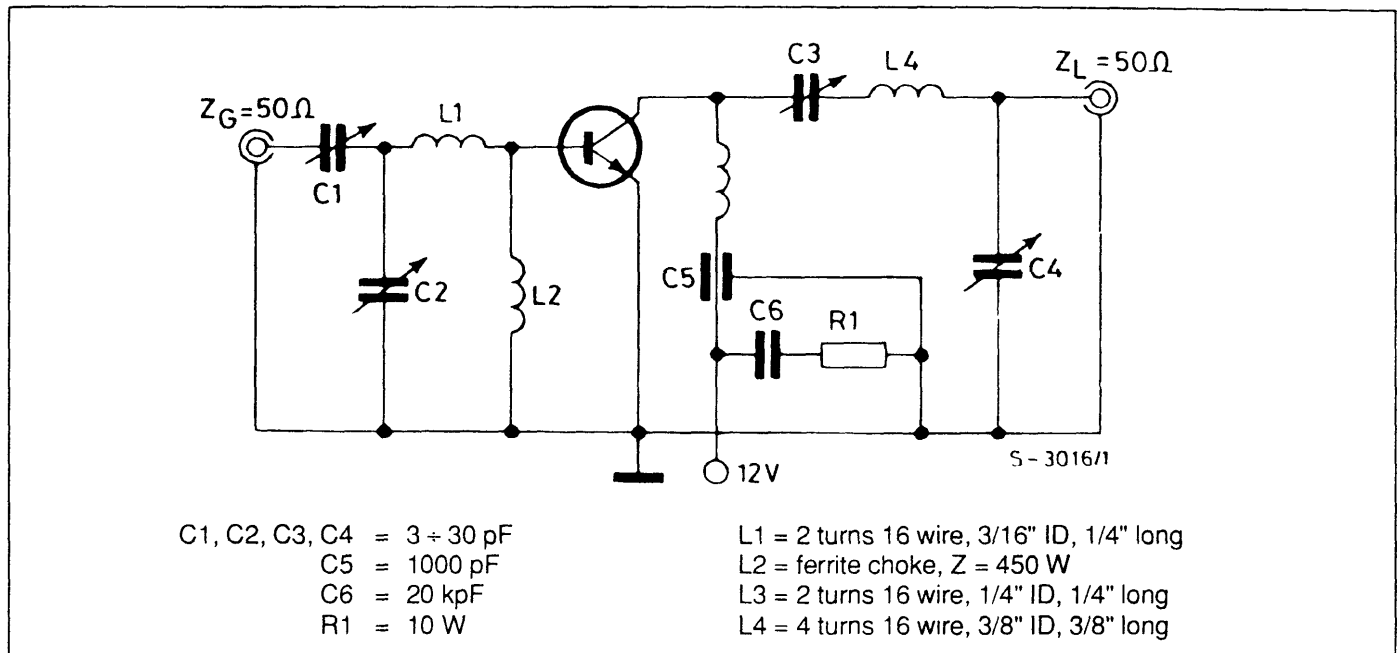
RF Output Power.



Collector-base Capacitance.



TEST CIRCUIT

Test Circuit for Power Output Measurement ($f = 175 \text{ MHz}$).

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.